

PART NUMBER 54F161^BFA

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All re-creations are done with the approval of the Original Component Manufacturer. (OCM)

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level

Qualified Suppliers List of Distributors (QSLD)

 Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OCM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

INCH-POUND
MIL-M-38510/343B
7 April 2004
SUPERSEDING
MIL-M-38510/343A
21 September 1989

MILITARY SPECIFICATION

MICROCIRCUITS, DIGITAL, BIPOLAR, ADVANCED SCHOTTKY TTL, BINARY COUNTERS, MONOLITHIC SILICON

Reactivated after 7 April 2004 and may be used for either new or existing design acquisition.

This specification is approved for use by all Departments and Agencies of the Department of Defense.

The requirements for acquiring the product herein shall consist of this specification sheet and MIL-PRF 38535

- 1. SCOPE
- 1.1 <u>Scope.</u> This specification covers the detail requirements for monolithic silicon, advanced Schottky TTL, binary counter microcircuits. Two product assurance classes and a choice of case outlines and lead finishes are provided for each type and are reflected in the complete part number. For this product, the requirements of MIL-M-38510 have been superseded by MIL-PRF-38535, (see 6.3).
 - 1.2 Part or Identifying Number (PIN). The PIN is in accordance with MIL-PRF-38535, and as specified herein.
 - 1.2.1 <u>Device types.</u> The device types are as follows:

Device type	<u>Circuit</u>
01	Synchronous 4 - bit binary counter (asynchronous master reset)
02	Synchronous 4 - bit binary counter (synchronous reset)
03	Synchronous 4 - bit up/down binary counter (with mode control)
04	Synchronous 4 - bit up/down binary counter
	(asynchronous master reset)

- 1.2.2 <u>Device class</u>. The device class is the product assurance level as defined in MIL-PRF-38535.
- 1.2.3 Case outlines. The case outlines are as designated in MIL-STD-1835 and as follows:

Outline letter	Descriptive designator	<u>Terminals</u>	Package style
E	GDIP1-T16 or CDIP2-T16	16	Dual-in-line
F	GDFP2-F16 or CDFP3-F16	16	Flat pack
Χ	CQCC2-N20 20	Square lead	dless chip carrier
2	CQCC1-N20 20	Square lead	dless chip carrier

Comments, suggestions, or questions on this document should be addressed to: Commander, Defense Supply Center Columbus, ATTN: DSCC-VAS, 3990 East Broad St., Columbus, OH 43216-5000, or emailed to bipolar@dscc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at www.dodssp.daps.mil.

AMSC N/A FSC 5962

1.3 Absolute maximum ratings.

Supply voltage range	-1.2 V dc at -18 mA to +7.0 V dc -65° to +150°C 303 mW +300°C (See MIL-STD-1835)
1.4 Recommended operating conditions.	
	5.5 V dc maximum
Minimum high level input voltage (V_{IH})	0.8 V dc
Low logic level	50 maximum
Width of clock pulse, high (PE = High) Device types 01, 02	9.0 ns minimum
Width of clock pulse, high (\overline{PE} = Low) Device types 01, 02 Width of clock pulse, low (\overline{PE} = High)	7.0 ns minimum
Device types 01, 02	8.0 ns minimum
Width of clock pulse, low (PE = Low) Device types 01, 02	9.0 ns minimum
Width of master reset pulse, low (MR = low) Device type 01	9.5 ns minimum
Width of PL pulse low: Device type 03 Device type 04 Width of clock pulse low:	
Device type 03	
Device type 04	7.0 ns minimum
Device type 04	6.0 ns minimum
Device type 04Setup time Pn high to clock pulse	12.0 ns minimum
Device types 01, 02 Setup time Pn low to clock pulse	5.5 ns minimum
Device types 01, 02 Setup time \overline{PE} or \overline{SR} high to clock pulse	5.5 ns minimum
Device types 01, 02	13.5 ns minimum
Setup time \overrightarrow{PE} or \overrightarrow{SR} low to clock pulse Device types 01, 02	10.5 ns minimum

^{1/} Must withstand the added P_D due to short-circuit test (e.g., I_{OS}).
2/ Maximum junction temperature shall not be exceeded except in accordance with allowable short duration burn-in screening condition in accordance with MIL-PRF-38535.

^{3/} The device shall fanout in both high and low levels to the specified number of inputs of the same device type as that being tested.

Setup time CEP or CET high to clock pulse	
Device types 01, 02 Setup time CEP or CET low to clock pulse	13.0 ns minimum
Device types 01, 02	7.5 ns minimum
Setup time U/D high to clock pulse	10.0
Device type 03	12.0 ns minimum
Device type 03	12.0 ns minimum
Setup time Pn high to PL Device types 03, 04	
Setup time Pn low to PL	0.0 110 11111111111111
Device types 03, 04	6.0 ns minimum
Setup time CE low to clock pulse	10.5
Device type 03	10.5 ns minimum
Device types 01, 02	2.5 ns minimum
Hold time Pn low to clock pulse Device types 01, 02	2.5 ns minimum
Hold time PE or SR high to clock pulse	
Device types 01, 02	2.0 ns minimum
Hold time PE or SR low to clock pulse	
Device types 01, 02 Hold time CEP or CET high to clock pulse	0.0 ns minimum
Device types 01, 02	2.0 ns minimum
Hold time CEP or CET low to clock pulse Device types 01, 02	2.0 ns minimum
Hold time Pn low to PL	
Device types 03, 04	2.0 ns minimum
Hold time U/D high to clock pulse	0.0
Device type 03	0.0 ns minimum
Device type 03	0.0 ns minimum
Hold time CE low to clock pulse	
Device type 03	0.0 ns minimum
Recovery time master reset to clock pulse Device type 01	6.0 ns minimum
Recovery time PL to clock pulse	
Device type 03	7.5 ns minimum
Device type 04	4.5 ns minimum
Recovery time \overline{PL} to CPU or CPD	
Device type 04	8.0 ns minimum

2. APPLICABLE DOCUMENTS

2.1 <u>General.</u> The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

2.2 Government documents.

2.2.1 <u>Specifications and Standards</u>. The following specifications and standards form a part of this specification to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-38535 - Integrated Circuits (Microcircuits) Manufacturing, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-883 - Test Method Standard for Microelectronics.

MIL-STD-1835 - Interface Standard Electronic Component Case Outlines

(Copies of these documents are available online at http://assist.daps.dla.mil/quicksearch/ or www.dodssp.daps.mil or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 <u>Order of precedence.</u> In the event of a conflict between the text of this specification and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Qualification</u>. Microcircuits furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturers list before contract award (see 4.3 and 6.4).
- 3.2 <u>Item requirements</u>. The individual item requirements shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein.
- 3.3 <u>Design, construction, and physical dimensions.</u> The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein.
 - 3.3.1 Terminal connections. The terminal connections shall be as specified on figures 1.
 - 3.3.2 Logic diagram. The logic diagram shall be as specified on figure 2.
 - 3.3.3 Truth table. The truth table shall be as specified on figure 3.
- 3.3.4 <u>Schematic circuits</u>. The schematic circuits shall be maintained by the manufacturer and made available to the qualifying activity and the preparing activity upon request.

- 3.3.5 Case outlines. The case outlines shall be as specified in 1.2.3.
- 3.4 Lead material and finish. The lead material and finish shall be in accordance with MIL-PRF-38535 (see 6.6).
- 3.5 <u>Electrical performance characteristics</u>. The electrical performance characteristics are as specified in table I, and apply over the full recommended case operating temperature range, unless otherwise specified.
- 3.6 <u>Electrical test requirements</u>. The electrical test requirements for each device class shall be the subgroups specified in table II. The electrical tests for each subgroup are described in table III.
 - 3.7 Marking. Marking shall be in accordance with MIL-PRF-38535.
- 3.8 <u>Microcircuit group assignment.</u> The devices covered by this specification shall be in microcircuit group number 12 (see MIL-PRF-38535, appendix A).

4. VERIFICATION

- 4.1 <u>Sampling and inspection.</u> Sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not effect the form, fit, or function as described herein.
- 4.2 <u>Screening.</u> Screening shall be in accordance with MIL-PRF-38535 and shall be conducted on all devices prior to qualification and conformance inspection. The following additional criteria shall apply:
 - a. The burn-in test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
 - b. Interim and final electrical test parameters shall be as specified in table II, except interim electrical parameters test prior to burn-in is optional at the discretion of the manufacturer.
 - c. Additional screening for space level product shall be as specified in MIL-PRF-38535.
 - 4.3 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-38535.
- 4.4 Technology <u>Conformance Inspection (TCI)</u>. Technology conformance inspection shall be in accordance with MIL-PRF-38535 and herein for groups A, B, C, and D inspections (see 4.4.1 through 4.4.4).
- 4.4.1 <u>Group A inspection.</u> Group A inspection shall be in accordance with table III of MIL-PRF-38535 and as follows:
 - a. Tests shall be as specified in table II herein.
 - b. Subgroups 4, 5, and 6 shall be omitted.
 - c. Subgroups 7 and 8 shall verify the truth tables herein.

TABLE I. <u>Electrical performance characteristics</u>.

Test	Symbol	Conditions	Device	Lir	nits	Unit
		-55°C ≤ T _C ≤ +125°C	type	Min	Max	
High level output voltage	V _{OH}	$V_{CC} = 4.5 \text{ V}, V_{IL} = 0.8 \text{ V},$	All	2.5		V
		I _{OH} = -1.0 mA, V _{IH} = 2.0 V				
Low level output voltage	V_{OL}	$V_{CC} = 4.5 \text{ V}, I_{OL} = 20 \text{ mA},$	All		0.5	V
	1	$V_{IH} = 2.0 \text{ V}, V_{IL} = 0.8 \text{ V}$				
Input clamp voltage	VIC	$V_{CC} = 4.5 \text{ V}, I_{IN} = -18 \text{ mA},$	All		-1.2	V
High layed inner to a company	1.	$T_C = 25^{\circ}C$	04 00		40	^
High level input current	I _{IH1}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 2.7 \text{ V}$	01, 02		40	μΑ
		V 55VV 70V	03, 04		20	^
	I _{IH2}	$V_{CC} = 5.5 \text{ V}, V_{IN} = 7.0 \text{ V}$	All		100	μΑ
Low level input current	I _{IL1}	V _{CC} = 5.5 V, V _{IL} = 0.5 V	01, 02	-0.0	-0.6	mA
			03, 04	03	-0.6	
	I _{IL2}	$V_{CC} = 5.5 \text{ V}, V_{IL} = 0.5 \text{ V}$	01, 02	-0.0	-1.2	mA
			03, 04	09	-1.8	
Short circuit output current 1/	I _{OS}	$V_{CC} = 5.5 \text{ V}, V_{OS} = 0.0 \text{ V}$	All	-60	-150	mA
Supply current	Icc	V _{CC} = 5.5 V	All		55	mA
Maximum count frequency	f _{MAX}	V _{CC} = 5.0 V	All	70		MHz
Propagation delay time,	t _{PLH1}	$V_{CC} = 5.0 \text{ V}, C_L = 50 \text{ pF} \pm 10\%,$	03	3.0	9.5	ns
CP to Qn		See figure 4				
CP to Qn	t _{PHL1}		03	5.0	13.5	ns
CPU, CPD to Qn	t _{PLH1}		04	3.0	10.0	ns
CPU, CPD to Qn	t _{PHL1}		04	5.5	14.0	ns
CP to Qn, $\overline{PE} = (high)$	t _{PLH1}		01, 02	2.0	9.0	ns
CP to Qn, $\overline{PE} = (high)$	t _{PHL1}		01, 02	3.5	11.5	ns
CP to TC	t _{PLH2}		03	5.0	16.5	ns
CP to TC	t _{PHL2}		03	4.5	13.5	ns
CPU to TCU	t _{PLH2}		04	2.5	10.5	ns
CPU to TCU	t _{PHL2}		04	3.0	9.5	ns

 $[\]underline{1}/$ Not more than one output should be shorted at a time.

TABLE I. <u>Electrical performance characteristics.</u>

Test	Symbol	Conditions	Device	Lin	nits	Unit
		-55°C ≤ T _C ≤ +125°C	type	Min	Max	
Propagation delay time, PL to Qn	t _{PLH3}	$V_{CC} = 5.0 \text{ V}, C_L = 50 \text{ pF} \pm 10\%,$ See figure 4	04	4.0	13.5	ns
PL to Qn	t _{PHL3}		04	5.0	15.0	ns
CPD to TCD	t _{PLH4}		04	2.5	10.5	ns
CPD to TCD	t _{PHL4}		04	3.0	9.5	ns
CP to Qn, $\overline{PE} = (low)$	t _{PLH2}		01, 02	2.0	10.0	ns
CP to Qn, \overline{PE} = (low)	t _{PHL2}		01, 02	3.0	10.0	ns
CP to RC	t _{PLH3}		03	3.0	11.5	ns
CP to RC	t _{PHL3}		03	3.0	12.5	ns
CP to TC	t _{PLH3}		01, 02	4.5	16.5	ns
CP to TC	t _{PHL3}		01, 02	4.0	18.5	ns
Pn to Qn	t _{PLH4}		03	2.0	9.0	ns
Pn to Qn	t _{PHL4}		03	6.0	16.0	ns
Pn to Qn	t _{PLH5}		04	1.5	8.5	ns
Pn to Qn	t _{PHL5}		04	6.0	16.5	ns
CET to TC	t _{PLH4}		01, 02	2.5	9.0	ns
CET to TC	t _{PHL4}		01, 02	2.5	9.0	ns
CE to RC	t _{PLH5}		03	3.0	9.0	ns
CE to RC	t _{PHL5}		03	3.0	9.0	ns
MR to Qn	t _{PHL5}		01	5.5	14.0	ns
MR to TC	t _{PHL6}		01	4.5	14.0	ns
PL to Qn	t _{PLH6}		03	5.0	13.0	ns
PL to Qn	t _{PHL6}		03	5.5	14.5	ns

TABLE I. <u>Electrical performance characteristics.</u>

Test	Symbol	Conditions	Device	Lin	nits	Unit
		-55°C ≤ T _C ≤ +125°C	type	Min	Max	
Propagation delay time,	t _{PLH6}	$V_{CC} = 5.0 \text{ V}, C_L = 50 \text{ pF} \pm 10\%,$	04	5.0	15.0	ns
MR to TCU		See figure 4				
MR to TCD	t _{PHL6}		04	5.0	16.0	ns
\overline{U}/D to \overline{RC}	t _{PLH7}		03	7.0	22.5	ns
U/D to RC	t _{PHL7}		03	5.5	14.0	ns
MR to Qn	t _{PHL11}		04	5.0	16.0	ns
Ū/D to TC	t _{PLH8}		03	4.0	13.5	ns
U/D to TC	t _{PHL8}		03	4.0	12.5	ns
PL to TCU	t _{PLH7}		04	6.0	18.5	ns
PL to TCU	t _{PHL7}		04	6.0	17.5	ns
PL to TCD	t _{PLH8}		04	6.0	18.5	ns
PL to TCD	t _{PHL8}		04	6.0	17.5	ns
Pn to TCU	t _{PLH9}		04	5.0	16.5	ns
Pn to TCU	t _{PHL9}		04	4.5	16.5	ns
Pn to TCD	t _{PLH10}		04	5.0	16.5	ns
Pn to TCD	t _{PHL10}		04	4.5	16.5	ns
MR to Qn	t _{PHL11}		04	5.0	16.0	ns

TABLE II. Electrical test requirements.

	Subgroups	(see table III)
MIL-PRF-38535	Class S	Class B
test requirements	devices	devices
Interim electrical parameters	1	1
Final electrical test parameters	1*, 2, 3, 7, 9, 10, 11	1*, 2, 3, 7, 9
Group A test requirements	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3, 7, 8, 9, 10, 11
Group B electrical test parameters when using the method 5005 QCI option	1, 2, 3, 7, 8, 9, 10, 11	N/A
Group C end-point electrical parameters	1, 2, 3, 7, 8, 9, 10, 11	1, 2, 3
Group D end-point electrical parameters	1, 2, 3	1, 2, 3

^{*}PDA applies to subgroup 1.

- 4.4.2 Group B inspection. Group B inspection shall be in accordance with table II of MIL-PRF-38535.
- 4.4.3 <u>Group C inspection.</u> Group C inspection shall be in accordance with table IV of MIL-PRF-38535 and as follows:
 - a. End-point electrical parameters shall be as specified in table II herein.
 - b. The steady-state life test duration, test condition, and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document control by the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005 of MIL-STD-883.
- 4.4.4 <u>Group D inspection.</u> Group D inspection shall be in accordance with table V of MIL-PRF-38535. End-point electrical parameters shall be as specified in table II herein.
 - 4.5 Methods of inspection. Methods of inspection shall be specified as follows:
- 4.5.1 <u>Voltage and current.</u> All voltages given are referenced to the microcircuit ground terminal. Currents given are conventional and positive when flowing into the referenced terminal.

	Device	type 01	Device	type 2	Device	type 03	Device	type 04
Terminal	Case	Case	Case	Case	Case	Case	Case	Case
number	E and F	X and 2	E and F	X and 2	E and F	X and 2	E and F	X and 2
1	MR	NC	SR	NC	P1	NC	P1	NC
2	СР	MR	СР	SR	Q1	P1	Q1	P1
3	P0	СР	P0	СР	Q0	Q1	Q0	Q1
4	P1	P0	P1	P0	CE	Q0	CPD	Q0
5	P2	P1	P2	P1	Ū/D	CE	CPU	CPD
6	P3	NC	P3	NC	Q2	NC	Q2	NC
7	CEP	P2	CEP	P2	Q3	Ū/D	Q3	CPU
8	GND	P3	GND	P3	GND	Q2	GND	Q2
9	PE	CEP	PE	CEP	P3	Q3	P3	Q3
10	CET	GND	CET	GND	P2	GND	P2	GND
11	Q3	NC	Q3	NC	PL	NC	PL	NC
12	Q2	PE	Q2	PE	TC	P3	TCU	P3
13	Q1	CET	Q1	CET	RC	P2	TCD	P2
14	Q0	Q3	Q0	Q3	СР	PL	MR	PL
15	TC	Q2	TC	Q2	P0	TC	P0	TCU
16	Vcc	NC	Vcc	NC	Vcc	NC	Vcc	NC
17		Q1		Q1		RC		TCD
18		Q0		Q0		СР		MR
19		TC		TC		P0		P0
20		V _{CC}		V _{CC}		V _{CC}		Vcc

FIGURE 1. <u>Terminal connections</u>.

Device types 01 and 02

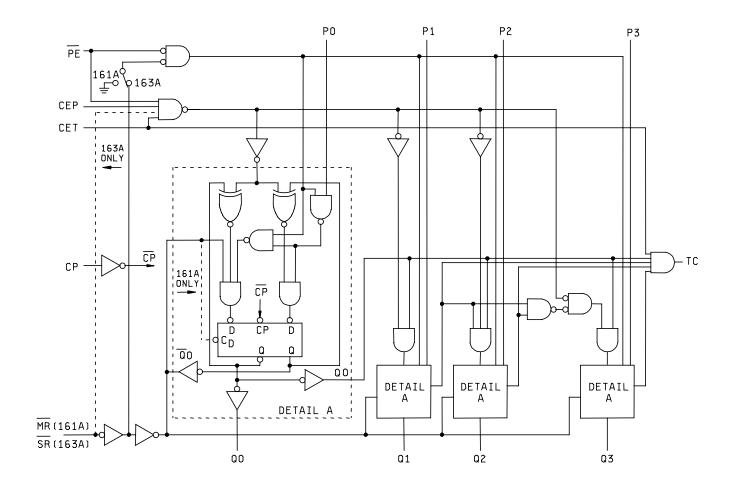


FIGURE 2. Logic diagram.

Device type 03

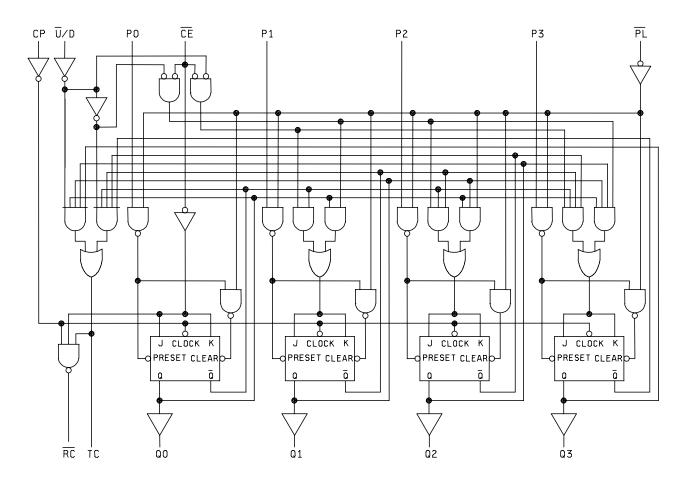


FIGURE 2. Logic diagram - Continued.

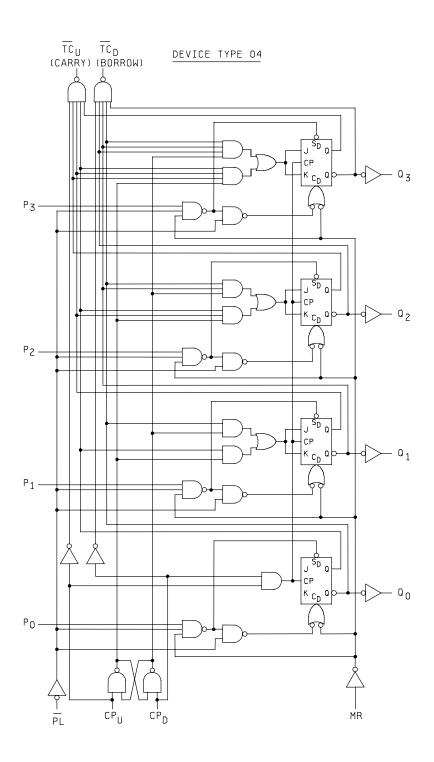


FIGURE 2. Logic diagram - Continued.

Device types 01 and 02

Mode select table

* SR	PE	CET	CEP	Action on the rising clock edge (_)
L	Χ	Χ	Χ	Reset (clear)
Н	L	Χ	Χ	Load (Pn - Qn)
Н	Н	Η	Η	Count (increment)
Н	Н	L	Х	No change (hold)
Н	Н	Х	L	No change (hold)

^{*} For F163A only

Device type 03

Mode select table

	Inp			
PL	CE	Ū/D	CP	Mode
Н	L	L		Count up
Н	L	Н		Count down
L	Χ	Χ	X	Preset (asyn)
Н	Н	Χ	Χ	No change (hold)

RC truth table

	Inputs	Output	
CE	TC*	CP	RC
L	Н	П	U
Н	Χ	Х	Н
X	L	X	Н

^{*}TC is generated internally H = High voltage level

Device type 04

Function table

MR	PL	CPU	CPD	Mode
Н	Х	Х	Χ	Reset (asyn)
L	L	Χ	Χ	Preset (asyn)
L	Н	Н	Н	No change
L	Η		Н	Count up
L	Н	H	Γ	Count down

H = High voltage level

FIGURE 3. Truth table.

H = High voltage level

L = Low voltage level

X = Immaterial

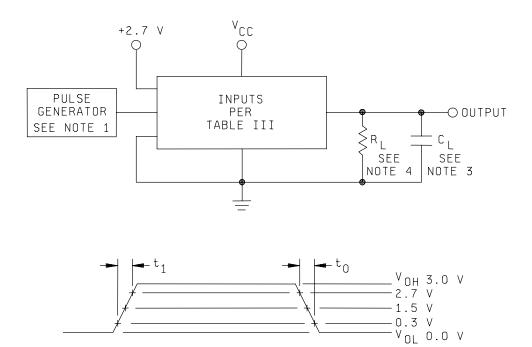
L = Low voltage level

X = Immaterial

⁼ One low level pulse

L = Low voltage level

X = Immaterial



NOTES:

- 1. $T_1 = T_0 \le 2.5 \text{ ns, PRR} \le 1 \text{ MHz, } Z_{OUT} \approx 50\Omega.$
- 2. Inputs not under test should be biased per table III.
- 3. $C_L = 50 \text{ pF} \pm 10\%$ including scope probe, wiring, and stray capacitance without package in test fixture.
- 4. $R_1 = 499\Omega \pm 5\%$.
- 5. Voltage measurements are to be made with respect to network ground terminal.

FIGURE 4. Switching time waveform.

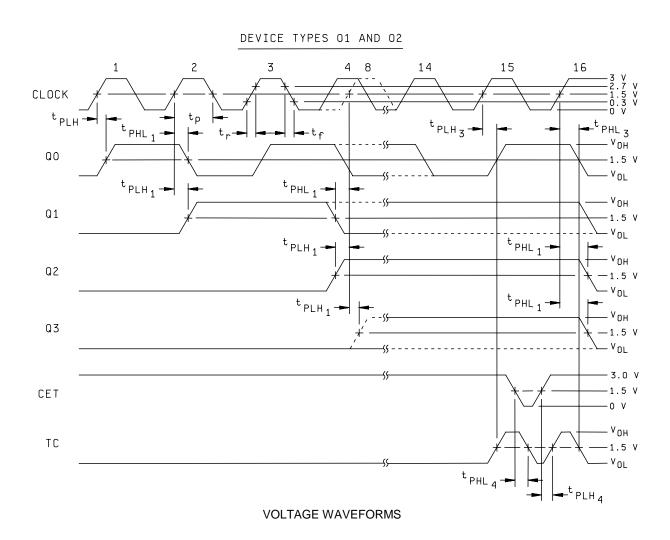
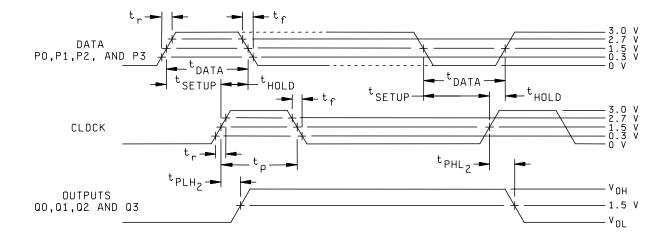


FIGURE 4. Switching time test circuit and waveforms for device types 01 and 02 - Continued.



NOTE: The data pulse generator has the following characteristics: V_{gen} = 3.0 V, $t_r \le$ 2.5 ns, $t_f \le$ 2.5 ns, t_{DATA} = 8.0 ns, t_{SETUP} = 5.5 ns, t_{HOLD} = 2.5 ns, $t_{P(CLOCK)}$ = 7.0 ns.

FIGURE 4. Switching time test circuit and waveforms for device types 01 and 02 - Continued.

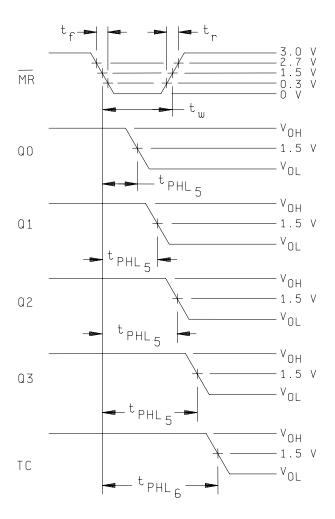
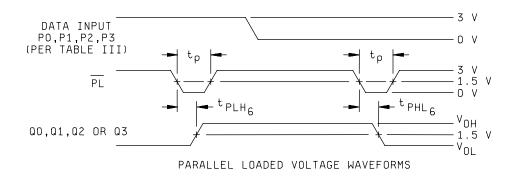


FIGURE 4. Switching time test circuit and waveforms for device type 01 - Continued.



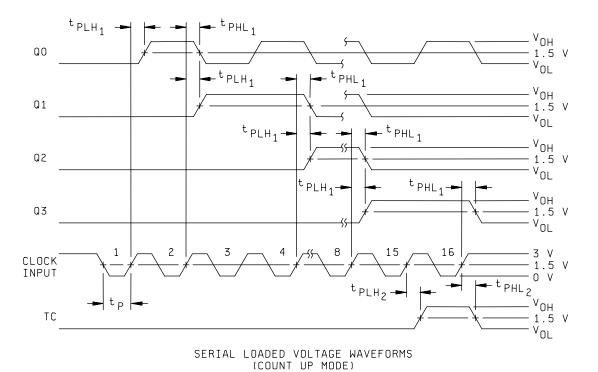


FIGURE 4. Switching time test circuit and waveforms for device type 03 - Continued.

DEVICE TYPE 03

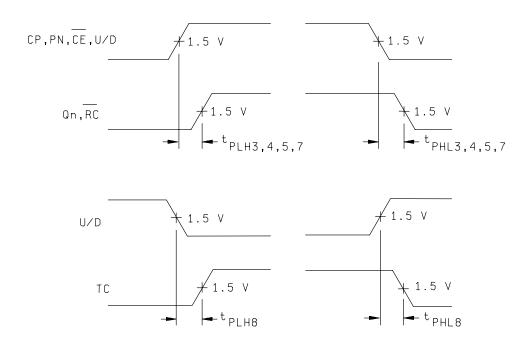
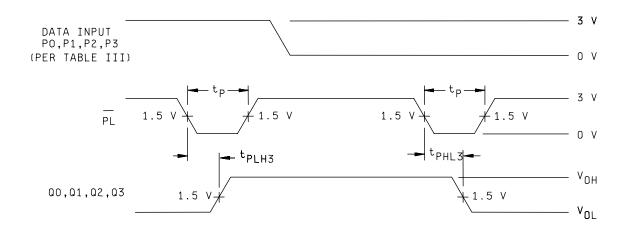
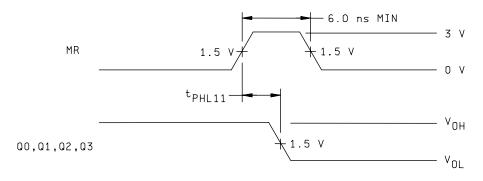


FIGURE 4. Switching time waveforms - Continued.

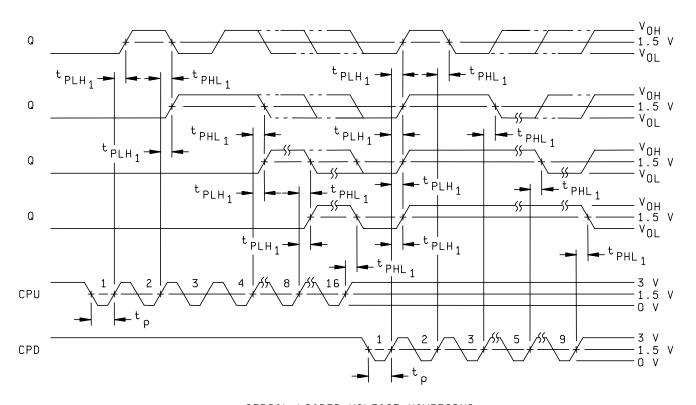


PARALLEL LOADED VOLTAGE WAVEFORMS



CLEAR SWITCHING VOLTAGE WAVEFORMS

FIGURE 4. Switching time test circuit and waveforms for device type 04 - Continued.



SERIAL LOADED VOLTAGE WAVEFORMS

FIGURE 4. Switching time test circuit and waveforms for device type 04 - Continued.

DEVICE TYPE 04

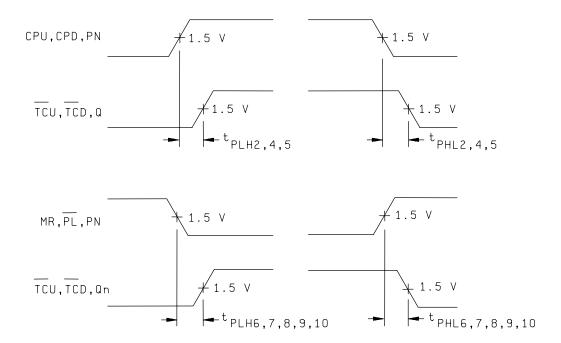


FIGURE 4. Switching time waveforms - Continued.

TABLE III. Group A inspection for device type 01. Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).

	Unit		>	=	=		=	-	-	=					=							μĄ	=	=	=		= :		=	=	=	=	=					-	=	mA	=	=	=	=	=	=	=	=
	ts	Max						0.5	=	=		= (-1.2		=			.				40	=			=				=	100	=							=	%	=	=	=	=			=	=
	Limits	Min	2.5	=	=		-																																	/≅		-	=	=		=		-
	Measured terminal		Q3	Q2	Q1	00	TC	Q3	Q2	Q1	00	CC	MR	CP	P0	P1	P.2	P3	CEP	Ш	CET	MR	S	P0	P1	P2	P3	CEP	肥	CET	MR	S	PO	P1	P2	F 13	CEP	Ш	CET	MR	8	PO	P1	P2	P3	CEP	띰	CET
16	20	Vcc	4.5 V	=	=	=	=	=	=	=					=			.	.			5.5 V	=					=		=		=						-			=	=	=	=			=	=
15	19	TC					-1.0 mA					20 mA																																				
14	18	8				-1.0 mA					20 mA																																					
13 13	17	ğ			-1.0 mA					20 mA																																						
12	15	Q2		-1.0 mA					20 mA																																							
9 10 11 0W	14	Q3	-1.0 mA	•				20 mA																																								
10 10	13	CET	5.5 V -′	=	=		2.0 V			=	= -	0.8 V									-18 mA							0.00	0.0 V	2.7 V							0.0 V	0.0 V	7.0 V							5.5 V	5.5 V	0.5 V
9 9	12	띰	0.8 V	=	-		>	=	=	=		-								-18 mA							\dashv	\dashv	2.7 V	0.0 V						+	0.0 V		0.0 V			0.0 V	-	=	H	5.5 V		5.5 V
8	10		GND	=	=		=	=	=	=					=			.	.			=	=				= :			=		=						=	-		=	=	=	=	-		=	=
6 7 8 8	6		5.5 V		=	=	=	=		=		-							-18 mA									2.7 V								7	۷ ۵۰/									0.5 V	5.5 V	5.5 V
	8		2.0 V				5.5 V	0.8 V			:	5.5 V						-18 mA	Ì								2.7 V									7.07									0.5 V			
4 5	7	P2		2.0 V			5.5 V	\dashv	0.8 V			5.5 V					-18 mA									2.7 V									7.0 V									0.5 V				
4	2	Ъ.			2.0 V		5.5 V			0.8 V	-	5.5 V				-18 mA									2.7 V									7.0 \									0.5 V					
8	4	P0				2.0 V	5.5 V				0.8 V	5.5 V			-18 mA									2.7 V									7.0 V									0.5 V						
2	6	8	2/		=	=	=	=		=		-		-18 mA									2.7 V									7.0 V									0.5 V							
-	7	MR	2/	=	=		=	5.5 V	=	=		= (-18 mA									2.7 V									7.0 V									0.5 V								5.5 V
Cases E, F	Cases 2, X 1/	Test no.	1	2	3	4	5	9	7	8	6			12	13	4 ,	15	16	1/	<u>8</u>	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46 4/
MIL-STD-		<u> </u>	3006	=	=		=	3007	<u> </u>	<u> </u>		= 0	3022	=	=		: :				=	3010	-	=	-					=	=	-	= :						-	3009	-		-	-	=	=	=	=
Σ	Symbol		V _{ОН}					OL					<u>0</u>									Ξ									IH2									111							7]	
	Subgroup		1	Tc = 25°C																											i																	

See footnotes at end of table III.

TABLE III. Group A inspection for device type 01 - Continued.

	Unit		μA	= .																																															
	Limits	Max	-150				- 1	22																																											
		Min	09-		.		=						1																					1															_	_	
	Measured terminal		Q3	Q2	ğ	000	ပ္ ;	Vcc		IIV	outputs	=	=				= :		=					= :				: =		=			=	=	=	=	н		=	н		н		=	=	= :		: =	=	=	
16	20	Vcc	5.5 V							/9	òi =	=	=		=	=	=	=	=			=	=	=		=	: :	:	:	=	=		=	=	=	=	"	и		"		"		=	=	=	: :	: =	=	=	-
15	19	72				1	0.0 V			_	J =	=	=		=	=		=	=	=	=	=	=	=		=				=	=	-	=	=	=	=	н	н	=	н	=	н	7	=	=		: :	= =	-	_ =	
41	18	පි				0.0 V				-	-	I	I	٦	_	I	I	_	_	I	I	_	7	I		=				, I	= 1		-	ı	I	_	7	I	I	7	_	I		=	=	-		: =	-		-
13	17	ō			0.0 V					_	1 :	=	=	I	=	=	= .	_	=			I	=	-		-		. -	-	-	=	I	=	-	=	_			=	I	=			=	-	-		: -	-	-	-
12	15	Q2		0.0 V							J =	-	=	-	=	-	= :	I	-	-	-	-	=	=		-				=	-		-	-	=	I			-		-		-	-	-	-		. -		J =	
4 5 6 7 8 9 10 11 12 13 1	41	Q3	0.0 V								J =	=	-		=	-	=	=	=	=	-	=	=	=		-			r =	-	=		=	-	=	-			-		-			=	-	-		: =			_
10	13	CET	5.5 V (α	2 ×	=	=		=	=	=		=				=	=		=				=	=		-	-	-	=			=		=		В	=	=	_	= <	∢ =	-	=	-
6	12	Ш					= 1	5.5 V		4	(=	=	-		=				=			=	=							=	-			_						н		н		=						α	
8	10		GND					:		CIND	2 =	=	-		=	=	_		=			-	=	-						-				-	-	-			=		=			=	=	_			_		_
	6		5.5 \ (. Postimo	mitted.			-	-		=	-	_		=			=	=	=	В	-	= <	∢ =			-		-	-	=	-								=	=				-	-	
9	80		5.5 V 5				5.5 V	0.0 V	and V. tests are omitted	R R) =	=	_		=	=	_		=			-	=	_						-				_	-	-			_		=			=	=	_			_		
2	7	P2	-	.5 V		4	_	0 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	and V.	and vo) =	-	_		-	-	_						=	_		-					-		-	_	-										-	-			_	-	_
4	2	P1		5.	5.5 V		5 \ 5	.0 V 0.	T55°C) =	=	_		=		-		=				=	-						-	-		-	_	-									=	=					-	_
3	4	P0			+	.5 \	5.5 \ 5	0 V 0.	1, except	l, categor) =	-	-		=				=			=	=							-			_	_	-	_					-			=	=				_		_
2	е	G G	2/			. 2	. 2	0 76.	dnoigane	Subgroup R	В	4	В	Α	В	A	В	A	В	٧	В	A	В	V	V	В	4 0	n <	۵ م	2 4	ς α	2 4		×	В	V	В	Α	В	Α	В	Α	В	В	A	В	∢ (20 0	ם ס	τ <	-
-	2	MR	5/				- 1	5 V C.	d limite as	2 m) A	-	-		-	_			-			-	=								-		-	-	=									-	-				_	-	_
Cases E, F	Cases 2, X <u>1</u> /	Test no.		48	49	20	51	$0.0 \times 0.0 \times 0.0$ 0.0×0.0	nditions an	53 an	54	55	56	22	58	59	09	61	62	63	64	65	99	29	89	69	70	17	73	74	75	92	2.2	78	62	80	81	82	83	84	85	98	87	88	88	06	91	26	23	94 0E	2
MIL-STD-	883 C method 2,		3011				_ [JU5 erminal co	erminal	114 T	<u> </u>	_	_	_	_	_	_				_		_	_	_	_					_	_	_		_	_	_			_		_	_								_
MIL-	Symbol 88		los 30					CC1 3(me feete t	nc- 30	tional	set	_																																					_	_
	Subgroup Syn		1	°c = 25°C				0 20			S 2	te																																							_

See footnotes at end of table III.

TABLE III. Group A inspection for device type 01 - Continued. Terminal conditions (pins not designated may be high $\geq 2.0~\text{V}$; low $\leq 0.8~\text{V}$; or open).

Subgroup Symbol	MI STD	-Cases	-	7	က	4	2	9	7	œ	თ	10		12	13	4	15	16			
			2	ဗ	4	2	7	8	o o	10	12	13	41	15	17	18	19	20	Measured terminal	Limits	Onit
		Test no.	MR	CP	PO	Ы	P2	P3	CEP	GND	Ш	CET	0 3	Q2	2	00	TC	Vcc		Min Max	_
7 Fur	ic- 3014	26	۷	A	4	A	٧	A	A	GND	В	A	I	I	I	I	I	/9	All		-
Tc = 25°C tional	īg	86	=	В	=	=		-	Α	=	-	=	I	I	I	I	I	-	outputs		
	:	66	В		-	-		-		-	-	-	_		7	_	_	=	=		
_		100	۷	-	=	=	=	-	-	=	=	-		_	7	_	_	=	=		
	=	101		∢	=	=	=	=	=	=	=	=	I	I	I	I	I	=	=		
	-	102		В	В	В	В	В	В	-		=	I	т	I	I	I				
		103		۷	В	В	В	В	В					7	١.	7	-	. :			
		104		א מ	∢ ∢	∢ ∢	∢ ∢	∢ ∢	∢ ∢	: =	: =	: =	- -	- -	- -	_ - - -	_ -	: :			
8 Rep	eat subgroup	Repeat subgroup 7 tests, at $Tc = 125^{\circ}C$ and $T_{c} = -55^{\circ}C$.	c = 125°C a	and $T_C = -5$:	5°C.																
_	× 3003	106	2.7 V	Z					2.7 V	GND	2.7 V	2.7 V				OUT		5.0 V	00	06	MHz
$\Gamma_{\rm C} = 25^{\circ}{\rm C}$ $\overline{2}/\ 9/$	<u>9</u> / Fig. 4	Ш	н								н	=			OUT				Q1		
	=	108												OUT					Q2		=
	=	109											OUT					=	Q3		
PLH1		110 8/	=													OUT			CP to Q0	2.0 7.5	su !
	=	111 "	=							н					OUT				CP to Q1		=
	=	112 "							-					OUT				=	CP to Q2	" "	=
	=	113 "	=								"		OUT						CP to Q3		=
PHL1		114 "	=							н	"					OUT			CP to Q0	3.5 10.0	. 0
	=	115 "								н	н	и			OUT			н	CP to Q1		н
	=	116 "								н				OUT					CP to Q2	" "	
	=	117 "								н	"		OUT						CP to Q3		=
PUH2	12	118 "							=		0.0 V					DUT			CP to Q0	2.5 8.5	=
	-	119 "								н					OUT				CP to Q1		=
	=	120 "	=	=					=					OUT				=	CP to Q2		=
	=	121 "								=			OUT					=	CP to Q3		=
PHL2	2	122 "	=	=					=	=		=				OUT		=	CP to Q0	4.0	=
	= :	123 "	-	= :						= :					OUT			_ :	CP to Q1		= :
		124 "											!	100					CP to Q2		
	.	125 "	= 1			,	1		.	.	= 1		OUT				ŀ	.	CP to Q3		
PLH3		126	2.7 V	Z	2.7 V	2.7 V	2.7 V	2.7 V			2.7 V						INO		CP to IC		
PHL3	.3	127	=	Z	=	=	=	=	=	=	2.7 V	=					=	=	CP to TC	`	-
PLH4	- 4	128		0.0 V		-					0.0 V	Z							CET to TC	2.5 7.5	
PHL4	. 4	129		2.7 V	=	-	=	-	=	=		Z					-	-	CET to TC		=
PHL5	-2	130	Z	0.0 V	=				=	=	0.0 V	2.7 V				T100		-	MR to Q0	5.5 12.0	0
	-	131		=		2.7 V					=	=			OUT				MR to O1		=
	-	132	=	=			27.7		=	=	=	=		Lic				=	2		=
		201												-					MR to Q2		
	-	133		-				2.7 V			=		500						MR to Q3	-	-
£	PHL6	134	=	=	2.7 V	2.7 V	2.7 V	2.7 V				=					OUT	=	MR to TC	4.5 11.5	2
10 San	e tests and	Same tests and terminal conditions as for subgroup 9, except $T_c = +125$ °C and use limits from table	itions as for	subgroup §	9, except	$T_c = +125^\circ$	C and use	limits from	table I.												
	ne tests, term	Same tests, terminal conditions and limits as for subgroup 10, except $T_C = -55$ °C.	s and limits	as for sub	group 10, t	except T _C =	= -55°C.]]]]]				

See footnotes at end of table III.

TABLE III. Group A inspection for device type 02.

		Unit		>					L				_	Ĺ			_					μĄ												L			_	_	mA	_		_					
		<u> </u>					Į	ļ	-	Ĺ												n							_	-									ш								
		Limits	Max					0		=	=	-	-1.2	-	=	=	=	-	= :	-	-	40	20	=		=		40	2 4	100	-		-	-	-		-	-	\S	=	-	=	=			=	=
			Min	2.5			=																																/8	=	=	=	=		-	=	=
		Measured terminal		Q3	Q2	ົ້ວໄດ້	3 E	2 8	36	0.1	00	10	SR	<u>8</u>	P0	P1	P2	Ь3	CEP	ш	CET	SR.	CP	P0	P1	P2	P3	<u>ا</u> ا ق	E F	3 18	ž g	දි සි	2 4	- B2	P3	CEP	믭	CET	8	P0	P1	P2	P3	CEP	SR	띰	CET
•	16	20	Vcc	4.5 V				=		=	=	-		-	=		=					5.5 V	=			=				=				=	=	н		=	-	=		=	=		-	=	=
	15	19	TC				-1 0 m	2				20 mA																																			
·	4	18	80	-1.0 mA					<u> </u>																																						
or open	13		۵ م	_	-1.0 mA			Č	20 mA	1																																					
0.8 V; c	8					Æ			20	20 mA																				-											-						
; low ≤	-		Q2		,	-1.0 mA	<u> </u>			20	4																				_																
≥ 2.0 V	=		03			,	-1.0 IIIA				20 mA	-									А															,	,	_						, .	_		_
e high	10	13	CET				700	+				0.8 V									-18 mA						+	0.00	+	7.7					H	0.0 V		7.0 V						5.5 \	5.5 \	5.5 V	0.5 V
d may b	თ	12	Ш	0.8 V			700	> =	=	=	=	=								-18 mA								0.0 V		> 0.0						0.0 V	7.0 V	0.0 V		0.0 V			=	5.5 \	5.5 V	0.5 V	2/
ignatec	ω	10	GND	GND			=	=	=	=	=	=		=	=		=			-		=	=			=			=	=			=	=	=		=	=	=	=		=	=	= :	=	=	=
not des	7	6	CEP	0.8 V								5.5 V							-18 mA								1	2.7 \		> 0.0						7.0 V	0.0 V	0.0 V						0.5 V	5.5 V	5.5 V	5.5 V
Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$; low $\leq 0.8 \text{ V}$; or open).	9	∞	Р3				2.0 \	> 0.			0.8 V	5.5 V						-18 mA									2.7 V								7.0 \								0.5 V				5.5 V
ndition	2	7	P2			2.0 V	7 2 7	> 0.0		780		5.5 V					-18 mA									2.7 V								7.0 /								0.5 V					5.5 V
ninal cc	4	2	P1		2.0 V		7 2 7	+	780	+		5.5 V				-18 mA									2.7 V								707	-							0.5 V						5.5 V
	က	4	P0	2.0 V			+	> 0.0	+			5.5 V			-18 mA	_								2.7 V								707	+							0.5 V	H						5.5 V
•	2	е	g G	2/				_	1	=	=	=		-18 mA	_								2.7 V	H					/ 0	71		۷۰۰/						2/	0.5 V	<u> </u>							2/ 6
	_	2	SR	2.0 V	5.5 V			=	_		_		-18 mA	-1								2.7 V	2							7.0 V	+	,							0						0.5 V		5.5 V
•	S II								<u> </u>																																						H
			Test no.	1	2	χ) ₄	4 μ	0	0 1	- α	ာ တ	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	27	i	29	Ġ	30	32	33	34	35	36	37	38	39	40	41	42	43	44	45	46 4/
	MIL-STD-	883 method		3006				7000	2000	=	=	-	3022	-	=	=	=	-		=		3010	=	=	=	=			=	=			-	=	=	=	=	=	3009	=		=	-		=	=	=
		Symbol		V _{он}					Ю				ıc									H								H2	!								Ξ							11.2	
		Subgroup		1	Tc = 25°C																																										
L		Ø		1	ř			_	>				>																																		\mathbf{L}

See footnotes at end of table III.

TABLE III. <u>Group A inspection for device type 02</u> - Continued.

		Unit	1	m.A	: :	=	=	=																																						
		Limits	Max	-150		=	=	22																																						
		ij	Min	09-		=	=																																							
		Measured terminal		Q3	20 02	00	12	Vcc		W	outputs		- -	-				=	=	=			. =	=	-					=				=	=				=	=	=				=	=
•	16	20	Vcc	5.5 V	: :	=		=		/9	il =			=		: :	=	=	=	н	= :		: :	=	=			"		=			= =		=		: :	=	=	=			: :	: :	=	=
	15	19	TC				0.0 V				-									н							н	"									- 3	- I	J =		н		ı.	Н	1 =	
	4	18	8	0.0 V								I	Ι-	-	I	Ι-	-	ı	I	7		r =	: =	=	=	٦	7	ェ	I -		ェ	I		ıΤ	I	7		c =	-	=	=		= :	-	<u> </u>	
or open	13	17	õ	H	0.0 V						l =		- 1	=] =	=		I				-		٦				= =				-		I		=		_	=				J =	
0.8 V;	12	15	02		0 /0	>											C =		L			<u> </u>			L								I =						-	L			_	+		_
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).					Č	-		_																															1							
≥ 2.0 \		14	_ Q3			0.0 V	H	>			=	-		=	-		=	=	-			-	=	=	-	I		-		-	-	-		=	-	-		=	-	-	=			-	1 =	-
be high	10	13	CET				5.5 V	-		æ	4	=		=	-		=	=	-	=				=	=	=		-		=	-	=		=	-	=		=	ď	i =	=	=	∢:		=	
d may	თ	12	l#	0.0 V	: :	=	=	5.5 V		4	=	=		=	=		=	=	=	=				=	=	=		-		=	-	=		=	=	=		=	-	=	=	=		: :	a) =
signate	∞	10	GND	GND		=	=	=	ted.	GND				=	=		=	=	=					=	=			=		=	=			=	=			=	=	=	=				=	=
not de	7	o	CEP				5.5 V	5.5 \	s are omit	B	<	=		=	=		=	=	=			: (n =	=	⋖	=		=		=	=	=		=	=	=		=	=	=	=	=			=	-
ns (pins	9	8	P3			5.5 V	5.5 V	0.0 \	V _{IC} tests	B B	=			=	=		=	=	=					=	=					=	-	=		=	=	=		=	-	=	=	=		: =	=	Α
ondition	2	7	P2		557	.0.0	5.5 V	0.0 V	125°C and	B	=				н											н	н					н				н				=		и			=	Α
minal c	4	2	Ъ.		5.5 V		5.5 V	0.0 \	pt Ic = +	B B	=			=			=	=	=	н					=		н					н		=						=					=	Α
	ო	4	P0	5.5 V			5.5 V	0.0 V	up 1, exce	up I, exce	=			=			=	=	=	н				=	=		н			=				=				=		=	=				=	Α
•	7	က	გ	2/	: :	=	=	5.5 V	as subgro	as subgio	m	A	a ⊲	c m	Α	ш <	τ α	Δ «	В	Α	а.	∢ <	۷ A	1 4	(M	Α	В	Α	В <	(M	ν «	В	< α	Δ «	В	Α	м <	τ α	0 00	1 <	В	Α	ω (В	٤ ٥	В
	-	2	SR	5.5 V		=		5.5 V	and limits	B	<	=		=			=	=	-					=	=			-		=	-			-	=	=		=	=	=	-				=	
	Cases E, F	Cases 2, X <u>1</u> /	Test no.		48	50	Ħ	52	Same tests, terminal conditions, and limits as subgroup 1, except 1 _C = +125°C and V _{1C} tests are omitted.	53	54	55	56	58	29	90	19	63	64	65	99	29	89 09	20	71	72	73	74	75	22	78	62	80	82	83	84	85	87	5 88	68	06	91	92	93	95	96
	MIL-STD-	883 method		3011		=	=	3005	ts, termin	3014	=	= :		=	-		=	=	=	=				=	=	=	=	-		-	-	-		=	-			=	=	=	=	-			=	
		Symbol		sol				20	Same tes	Func-	tional	test	_																																	
		Subgroup		-	Tc = 25°C				7 6		5°C		2																																	

See footnotes at end of table III.

TABLE III. Group A inspection for device type 02 - Continued. Terminal conditions (pins not designated may be high $\geq 2.0~\text{V}$; low $\leq 0.8~\text{V}$; or open).

	Unit													MHz	=	=		ns	=				=	-	=	=				=		=	-	-		-				
	its	Max	İ															7.5	=	=	=	10.0		=	=	8.5	н	=		=	=	=	=	14.0	16.0	7.5	7.5			
	Limits	Min												06	=	=	=	2.0	=			3.5				2.5	н			4.0	=	-	=	4.5	2.0	2.5	2.5			
	Measured terminal		IIA	outputs		=					=			00	ğ	02	0 3	CP to Q0	CP to Q1	CP to Q2	CP to Q3	CP to Q0	CP to Q1	CP to Q2	CP to Q3	CP to Q0	CP to Q1	CP to Q2	CP to Q3	CP to Q0	CP to Q1	CP to Q2	CP to Q3	CP to TC	CP to TC	CET to TC	CET to TC			
16	20	Vcc	/9		=					н	=			5.0 V	=							н					н									н				
15	19	TC	I	=	=	_	_	I	Ŧ	Г	7	I																						OUT		"				
4-	18	8	I			7	_	I	н	٦	7	I		DOUT				OUT				OUT				OUT				OUT										
13	17	۵ 1	I	-	=	_	_	I	I	٦	7	I			DUT				OUT				OUT				OUT				DUT									
11 12 13	15	Q2	I	-		7		I	н	7	7	I				OUT				OUT				OUT				OUT				OUT								
=	14	0 3	I	-	=	_	_	н	н	7	7	н					OUT				OUT				OUT				OUT				OUT					5		
ı	13	CET	⋖	-	-	-	-	-			-	-		2.7 V	-	-		-		-	-			-		0.0 V		-			-	-		2.7 V	2.7 V	N	Z			
6	12	쁘	В	-	=	=	_				-			2.7 V			-	=	=							0.0 V				=	-	-	=	. 7/	2.7 V	0.0 V	0.0 V			
8	10	GND	GND	=			-	-			=	-		GND		-		-		=	=			=		-		=	=			=	-	=	=					
	6	CEP	۷	A			-		В	В	A	Α		2.7 V		-						н	н				н									н		table I.	:	
4 5 6 7 8 9 10	ω	P3	4	-	=	-	-		В	В	A	A																						2.7 V		н		and use limits from table		
2	7	P2	4	-	=	=	=		В	В	V	٧																						2.7 V				and use l	-55°C.	
4	2	7	4	=	-	-	=	-	В	В	A	A																						2.7 V	=		-	c = +125°C	xcept T _C =	O
e e	4	6 0	4	=		-	=		В	В	٧	Α	Š.																					7/	2.7 V			except T	roup 10, e.	,
2	က	G G	4	В	В	A	В	A	В	Α	В	A	$10^{\circ} - 55^{\circ}$	Z	=	=	=	=	=						"	=				=	=	=	=	Z	Z	0.0 V	0.0 V	ubaroup 9	s for subg	
-	7	SR	⋖	٧	В	В	٧		н	н			125°C an	2.7 V	=			2/				н	н		н	2.7 V	н							2.7 V		н		ns as for s	and limits a	
Cases E, F	Cases 2, X <u>1</u> /	Test no.	26	86	66	100	101	102	103	104	105	106	Repeat subgroup 7 tests, at $Tc = 125^{\circ}C$ and $T_{c} = -55^{\circ}C$.	107	108	109	110	111 <u>8</u> /	112 "	113 "	114 "	115 "	116 "	117 "	118 "	119	120	121	122	123	124	125	126	127	128	129	130	Same tests and terminal conditions as for subgroup 9, except $T_c = +125^{\circ}$ C	Same tests, terminal conditions and limits as for subgroup 10, except $T_C =$	
MIL-STD-	883 method	<u></u>	3014	_	=	<u> </u>	_		-	=			group 7 tes	3003	Fig. 4	-	_		_	-	-		=	-	=		=	-			_	_	_					and termir	terminal	
III			Func-	ional	test		_						epeat sub	f _{MA} ×	7/ 9/ F			PLH1				PHL1				PLH2				PHL2				PLH3	PHL3	PLH4	PHL4	ame tests	ame tests	
	Subgroup Symbol		7 F	Tc = 25°C ti									8 R	6	ပ္ပ			l												<u> </u>								10		1

See footnotes at end of table III.

TABLE III. Group A inspection for device type 03. Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).

		Onit		>	=		=	=		н	=				=	=	=	=	н	=			hΑ	=	=			=			=	=	=	=		=		=	mA	-	E	н	=	=	=	
		its	Мах						0.5	н			=		-1.2		=	=	н	-	=	"	20			"	=		"		100	=			=	-			3/			н				=
		Limits	Min	2.5	=		=	=																															3/	-		ш	=	=		=
		Measured terminal		Ω1	Ø0	Q2	5 L	2 2	Q1	Q0	Q2	Q3	2	RC	P1	CE	Ū/D	P3	P2	김	S	P0	P1	프	Ū/D	P3	P2	딤	CP	P0	P1	삥	Ū/D	P3	P2	Ŋ	SP	P0	P1	Ū/D	P3	P2	님	S	P0	<u>CE</u>
9	16	20	Vcc	4.5 V	= :		=	=			=				=	=		=			=		5.5 V		=		=			н	=	=			=				=						=	=
	15	19	9 0		2.0 V		700	2.0 V		0.8 V			2.0 \	> 0:4								-18 mA								2.7 V								7.0 V							0.5 V	
(c)	14	18	CP				700	2.0 V					7 8 0	> 0.0							-18 mA								2.7 V								7.0 V							0.5 V		
; or ope	13	17	12					-1.0 mA					20 mA																																	
\ ≤ 0.8 V	12	15	J				-1 0 m	+					20 mA																																	
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).	11	41	님	0.8 V							=									-18 mA			5.5 V			5.5 V	5.5 V	2.7 V		5.5 V	5.5 V			5.5 V	5.5 V	7.0 V		5.5 V	0.0 V		0.0 V	0.0 V	0.5 V		0.0 V	
igh ≥ 2.	10	13	P2			2.0 V	700	2.0 V			0.8 V		2.0 V	> 0.1					-18 mA							H	2.7 V								7.0 V							0.5 V				
nay be h	6	12	Р3				V.0 v "	=				\dashv	2.0 V					-18 mA								2.7 V								7.0 V							0.5 V					
gnated r	8	10	GND	GND	= :			-	=						=	=	=	=		=	=		н	=	=		=	=			=	=	=		=	=			=	-		ш	=		=	=
not desig	,	თ	O3			4	-1.0 IIA					20 mA																																		
s (pins ı	9	ω	Ø2			-1.0 mA					20 mA																																			
ondition	ç	7	Ū/D				\ a 0	0.8 \					2.0 \	9			-18 mA								2.7 V								7.0 V							0.5 \						
rminal c	4	2	병	2.0 V	=		\ a \	0.8 \	2.0 V				/ 8 0	5		-18 mA								2.7 V								7.0 V														0.5 V
	3	4	00		-1.0 mA					20 mA																																				
(7	က	ğ	-1.0 mA					20 mA																																					
,	1	2	Ъ.	2.0 V			700	2.0 \	0.8 V				2.0 V	> 0:4	-18 mA								2.7 V								7.0 \								0.5 V							
ď	Cases E, F	Cases $2, \times \underline{1}$	Test no.	+	2	e -	4 π	၁ မ	7	8	6	10	11	7	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28	29	30	31	32	33	34	35	36	37	38	39	40	4	42	43	44
	MIL-STD-	883 method		3006	=			-	3007	=	=		-		3022	=	=	=	=	=	=		3010	=		-		=	=	=	=	-	=	=	=	=	=	=	3009	-	=	=	=	=	=	=
-				V _{он}					OL.						2								H								H2								171							11.2
		Subgroup Symbol		-	Tc = 25°C																			_	_					•			_													

See footnotes at end of table III.

Unit ₩. 22 Max -150 Limits Min 09-Measured terminal 2828518 Vcc 20 5.5 V 5.5 V 15 19 Ъ 5.5 V 5.5 V TABLE III. Group A inspection for device type 03 - Continued. Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open). 18 CP 0.0 V RC 0.0 V 2 15 14 Ы 5.5 V 5.5 V 13 P2 12 Р3 GND GND 10 0.0 V Q3 Q2 0.0 V 0.0 V Ū/D 0.0 V 0.0 V CE õ 8 Repeat subgroup 7 at $T_c = 125^{\circ}C$ and $T_c = -55^{\circ}C$. See footnotes at end of table III. ğ 3 5.5 V Ы Cases 2, \times 1/ Test no. Cases E, F 65 66 67 66 67 67 77 77 77 75 75 45 46 47 48 48 49 50 MIL-STD-883 method 3011 Symbol 7 Tc = 25°C 1 Tc = 25°C

TABLE III. Group A inspection for device type 03 - Continued.

						F	erminal	conditic	ans (pins	Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$; low $\leq 0.8 \text{ V}$; or open).	ignated	may be	$high \ge 2$.0 V; lo	v ≤ 0.8 V	; or ope	(u						
		MIL-STD-	Cases E, F	-	2	က	4	2	9	7	∞	6	10	11	12	13	41	15	16				
Subgroup	lodmyS dr	n 883 method	Cases 2, X <u>1</u> /	2	က	4	2	7	80	6	10	12	13	41	15	17	18	19	20	Measured terminal	Limits	ts	Unit
			Test no.	Ы	ğ	8	빙	Ū/D	07	Q3	GND	P3	P2	김	20	122	Q S	P0	Vcc	ı	Min	Max	
6		3003	66			OUT	GND	GND			GND			2.7 V			Z		5.0 V	00	90		MHz
$T_{c} = 25$,C	Fig. 4	100		OUT		= :	=			= :			= :			= :		=	Q1			
			101				: :		OUT	TUO										03			
- t	PLH1	=	103		Ì	DUT					=			2/			=		=	CP to Q0	3.0	7.5	ns
		=	104		OUT						=								=	CP to Q1			"
			105						TUO	į										CP to Q2			
			106			Ė				DO	- -									CP to Q3	= [= ;	
-	PHL1		107		TUO	Ino														CP to CO	5.0	11.0	: :
			109						TUO		-			=			=		=	CP to Q2	=	=	=
			110							OUT										CP to Q3			"
t _	PLH2		111	2.7 V								2.7 V	2.7 V		OUT			2.7 V		CP to TC	6.0	13.0	"
_	PHL2		112	=										-	OUT		-			CP to TC	5.0	11.0	
<u>+</u>	PLH3		113	-								-	=	-		DOL	-	2.7 V	-	CP to RC	3.0	7.5	=
_	PHL3	=	114								=	=		=		OUT	=		=	CP to RC	=	7.0	
+	PI H		115	=		DOUT	2.7 V	2.7 V			=	=	=	=			2.7 V	Z		Po to Qo		7.0	=
		=	116	Z	OUT		=	=			=							2.7 V	=	P1 to Q1		=	"
		-	117	2.7 V			-	-	OUT		=		Z	=			=		-	P2 to Q2		-	
			118	- -		Ė	- -	- -		DO	- -	2	2.7 \					= 2		P3 to Q3	= 0	= (
-	PHL4		119	: <u>Z</u>	THO	100	: =	: =			: =	2.7 \		: =			: =	N 2 2		P0 to Q0	6.0	13.0	
		-	121	2.7 V	0		=	=	TUO		=	=	Z	=			=	=	=	P2 to Q2	=	-	
			122	н			=			OUT	н	Z	2.7 V						н	P3 to Q3	н		
-	PLH5		123				Z					2.7 V				TUO			=	CE to RC	3.0	7.0	=
	PHL5	-	124	=			Z				=	=	=			OUT		=	-	CE to RC	3.0	7.0	
+	РГН6	-	125			OUT	2.7 V	2.7 V						z			2.7 V	2/	-	PL to Q0	5.0	11.0	=
			126	/7	TUO		=	-			=		=					2.7 V	=	PL to Q1		=	
			127	2.7 V			=	=	OUT		-	=	2/	=			=	-	=	PL to Q2	=		
			128	=			=	=		OUT	=	2/	2.7 V	=			=	=	=	PL to Q3	=	=	
+	PHL6	-	129	=		OUT						2.7 V						0.0 V	-	PL to Q0	5.5	12.0	"
			130	V 0.0	TUO		-	-			=	=	=					2.7 V	=	PL to Q1			
			131	2.7 V			=	=	OUT		=	=	0.0 V	=			=	=	=	PL to Q2	=	=	
			132	2.7 V			=	-		TUO	=	0.0 V	2.7 V	=				=	=	PL to Q3		=	
_	PLH7		133					Z			=			77		OUT			-	U/D to RC	7.0	18.0	
_	PHL7		134					=			=			=		TUO			=	Ū/D to RC	5.5	12.0	
_	PLH8		135					=			=			=	OUT				=	Ū/D to TC	4.0	10.0	
_	PHL8		136					=			=				OUT				-	U/D to TC	4.0	10.0	
10	Same	Same tests and terminal conditions as for subgroup 9, except $T_{\rm C}$ = +125°C and use limits from table Same tests, terminal conditions and limits as for subgroup 10, except $T_{\rm C}$ = -55°C.	minal conditi	ions as for and limits	subgroup as for sub	9, except group 10	$t T_c = +12$, except T	5°C and us c = -55°C.	se limits fro	m table I.													

See footnotes at end of table III.

TABLE III. Group A inspection for device type 04.

		Onit		^	н	=	=	=	=		=	=		=	=			н	=		=	=		μA	=	=	=	= :	=			=	=		=	=		=	=	mA	=		=	=	=	= =
		iits	Мах							0.5	-	=			-	-1.2	-		-	-	=	-	-	20	=	-	=	- :	-	-	-	100	=		-	-		=	=	3/	=	-		-	=	
		Limits	Min	2.5	н	-	=	=	=																															3/	=	=			=	
		Measured terminal		Q1	Q0	Q2	Q3	뎔	TCD	Q1	Q0	Q2	Q3	ΤŒ	<u>TC</u> D	P1	CPD	CPU	P3	P2	P.	MR	P0	P1	CPD	CPU	P3	P2	F	MR	P0	P1	CPD	CPU	2 5	7	PL	MR	P0	P1	P3	P2	님	MR	PO	CPD
:	16	20	Vcc	4.5 V	и		=	-	=			=				=				=				5.5 V		=	=		-				=		=	=				=	=	=	-	-		
	15	19	P0		2.0 V			5.5 V	0.0 V		0.8 V			5.5 V	0.0 V								-18 mA								2.7 V								7.0 V						0.5 V	
n).	4	18	MR	0.8 V	"	-	-		=	0.0 V	=	=	= (0.8 V	0.0 V							-18 mA								2.7 V								7.0 V		0.0 V	=	=		0.5 V	0.0 V	
or ope	د	17	18						-1.0 mA						20 mA																							П								
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open)	12	15	일					-1.0 mA	-					20 mA																																
V; low	-	41	김	0.8 V		-	=	-	=		=	=									-18 mA								2.7 \							707	» •	H		0.0 V	=	=	0.5 V		0.0 V	
igh ≥ 2.(6	13	P2)		2.0 V		5.5 V	0.0 V			0.8 V		5.5 V	0.0 V					-18 mA	-							2.7 V								› O. /		H			-	0.5 V				
ay be h	<u></u>	12	P3			\dashv	2.0 V		0.0 V				0.8 V		0.0 V				-18 mA	-1							2.7 V	.,							\ O.\			H			0.5 V	_				
ated m	∞	10		GND		_	2	<u>د</u>	0					2	0				-1			=												1 =	` 	_	_	=	=	-	0	=	_	-		
t design		б	Q3 G	Э			-1.0 mA						20 mA																								_	H								
pins not		ω	Q2 C			-1.0 mA	-1.0					20 mA	20																																	-
ditions (2		CPU			-1.(2.0 V	5.5 V			20		0.8 V	5.5 V			-18 mA								2.7 V								7.0 V				H								5.5 V 0.5 V
nal con	4		CPD CI				+	5.5 V 2.0	2.0 V 5.8				+		0.8 \ 5.4		-18 mA	_							2.7 V	2.							+	7.(H							Н	+
					mA			5.6	5.0		μA			5.6	3.0		-18								2.7								7.0 V	1	1	1	_	H			_					0.5 V 5.5 V
-	m		00		-1.0 mA					\vdash	20 mA																							1	-	-	_				_					+
-	7	က		V -1.0 mA				>	>	V 20 mA			-	>	>	hA								^								^								^						1
-	ς, -	s 7	o.	2.0 V				5.5 \	0.0 V	0.8 V				5.5 V	0.0 V	-18 mA								2.7 V								7.0 V						H		0.5 V						+
	Cases - E, F	Cases $2, \times 1/$	Test n	-	2	3	4	2	9	7	8	6	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	52	26	27	28	29	30	33	32	50	ţ	35	36	37	38	39	40	41	42	44
	MIL-STD-	883 method		3006	-	-	-	=	=	3007	-	=			=	3022	=	=	-	=	=	-		3010	=	=	-		-	=	-	-	-		-	-		=	=	3009	=	=	-	-	=	
		Symbol		V _{он}						OL)								Ħ								IH2								111						7
		Subgroup		_	$Tc = 25^{\circ}C$																			_								_						_		_						

See footnotes at end of table III.

TABLE III. Group A inspection for device type 04 - Continued.

		Onit		mA	=		-			=																																					
		ts	Max	-150			=			22																																					
		Limits	Min	09-																																											
		Measured terminal		۵1	۵0	Q2	3 5	3	TCD	Vcc		ΠΔ	outputs	. =	=	: :			=	=	=	=		=			=		=						=	=		= :				: -	: =	=	=	=	
	16	20	Vcc	5.5 V	=		-			=		/9	òl =	=				: :		-		-					=	=	=		"	-				:	"		: :	: :	= :	: :	: :	=	=		= =
	15	19	P0		5.5 V		5.5 V		0.0 V	5.5 V		٨	ζ =		В				=	=	-	-	н			=		=	=	-		Α				=			.				=	=	=	=	
n).	4	18	MR	0.0 V			-			=		٥	(m	=	=		-	-	=	-	=	-				=	-	=	=	=					-	=			= (а :			=	=		=	
or ope	13	17	18						0.0 V			ı	-	=			-		-	-	-	-				=	=	=	=	-					-	=							-	=	-	_	ΙI
< 0.8 V;	12	15	ם				0.0 V	+				_	-	=	=		-		=	-		-				=	=	=	=	=		=			-	-				_					ıΞ	=	
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).		41	님	0.0 V						=		۵	(M	A	A	ω «	∢ =		=	-	-	-	н			=	-	=	=	-		н				=							: =	=	=	=	
igh ≥ 2.0	10	13	P2)		5.5 V			0.0 V	5.5 V		٥	(=	=	В			: =	-	-	-	-				-	=	=	=	-		А			-	=				_	= :			-	-	-	
ıay be h	6	12	Р3			_	5.5 V	+		5.5 V		٥	ζ =	=	В					-		-				-			=	-		Α			-					_				_	-	=	
nated m	8	10	GND	GND			=	-		=		CINE	2 =	=			-		-	-		-				-	-	-	=	-					-	=				_	= r			-	-	=	
t design		6	03	0		2	> 0.0				omitted.			-] =	_		-	_	J =	-				_	_	-	-	-	I				-	=								-	_		エエ
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nal con	4	2	CPD C				5.	-		5.5 V 5.	C = +125	_ce-= o	(=	_					_		_	_				_	_		_	_					_	_			_	_				_	_	В	B A
	en en	4	00 C		0.0 V				5.	2.	except -	, except								<u> </u>		ı	Н	٦	_		-		ı H	ı			T :				н	7	_	Η:	+	+	_ _ _	_ 	<u> </u> -		II
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		2						-	^ _	> .	limits as	TIMES AS			В		1		-					1		-	_		-	-						_			1	1	+		+	-	<u> </u>		
	es T			5.5 V		1	-			5.5 V	tions, and	and,]				+		-		-						+								-						+	+		-	Ĺ		
	Cases D- E, F		Test no.	45	46	47	49	I		21	Same tests, terminal conditions, and limits as subgroup 1, except $T_c = +125^{\circ}C$ and V_{1c} tests are omitted.	IIIIai coridi	53	54	22	56	20	22	80	8 6	62	63	64	65	99	68	8	20	7	72	73	74	75	9/	78	79	80	81	82	83	84	g g	87	388	88	06	91
	MIL-STD-	l 883 method		3011	=					3005	tests, term	3014	=	=	=		-	-	-	-	-	-	-	=		-	-	=	=	-	=	-			-	-	-	-					-	-	-	=	
		Symbol		sol						00	Same	Fing			\																																
		Subgroup		-	$Tc = 25^{\circ}C$						7 %	0 1	Tc = 25°C		2																																

See footnotes at end of table III.

TABLE III. Group A inspection for device type 04 - Continued.

		Onit																														MHz "	=	=	=	=	=	=	ns	- -	=	=	=	=	=	=		=		- -	=	=
		iits	Мах																																				8.5			=		=	=	12.5	-	=		-	=	=
		Limits	Min																													06	: =		=	=	=	н	3.5			=			=	5.5						=
		Measured terminal		All	outputs				-			=										: :	:	: =	=	=				=		CPU to Q0	CPU to Q1	CPU to C3	CPD to Q0	CPD to Q1	CPD to Q2	CPD to Q3	CPU to Q0	CPU to Q1	CPU 10 Q2	00.00	CPD to O1	CPD to Q2	CPD to Q3	CPU to Q0	CPU to Q1	CPU to Q2	CPU to Q3	CPD to Q0	CFU 18	CPD to Q3
•	16	20	Vcc	/9		=	=	: :	=	=	=		=	=	=	-	-					: :		: :	Ξ	=			=			5.0 V		=	=	=		=	= :		=	=		=	=	=	=					=
	15	19	Po	Α		=	=		=					=	В			н			.							=		н									0.0 V			700	v 0.0							7,00	v u.o.	
n).	4	18	MR	В		=	=		=		-		=		-	-									=		=	=		=		GND "		=	=	=	-		0.0 V			=			-		=	=		- -		=
or ope	13	17	12	т		=	=		-		-		=	=		-	-				.				=	-	=	=	-																					1		1
≤ 0.8 V	12	15	TGT	I	-	=	=		=	-	=		-	=							.				=	=	=	=	=																					1		
Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$; low $\leq 0.8 \text{ V}$; or open)		14	님	Α		=	-		-		-		=	=	-	-	-								-	-	=	=	-		•	2.7 V	: =	-	=	=		-	5/			-		-	=	-	-					=
$igh \ge 2.0$	10	13	P2	٧		=	=		=		=		=	=		В	=								=	=	=	=	=										0.0 V			// 0 0	A 0.0	V 0.0	=	=			-	0.0 V	> 0.0	0.0 V
ıay be h	თ	12	P3	Α					=	-			=	=	-	В		н							=		=											-	0.0 V			-			0.0 V	=	-		= 7			ŀ
nated rr	∞	10	GND	GND	-	=	=		=	-			=	=	-		-		-		.				=	=	=	=	=	=		GND =	: =	=	=	=		=			=	-		=	-	=	-		= :		=	=
ot desig	7	6	03	I		=	-		-		-		=	-							.				=		=	-						LIO	5			OUT			Ŀ	5			OUT				OUT	+	-	DUT
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	Cases E, F	Cases 2, X <u>1</u> /	Test no.	93	94	92	96	97	000	33	101	102	103	104	105	106	107	108	109	110	111	112	113	114	116	117	118	119	120	121	Repeat subgroup 7 at $T_c = 125$ °C and $T_c = -55$ °C.	122	123	125	126	127	128		1	131 (132	137			137							145
		883 C method 2,	1	3014		_							_	_	_	_	_	_	_				1		_	_	_	_	_		roup 7 at		4 = 4		_	_	╚					<u> </u>		_	_		_			<u></u>		
	MIL.	Symbol 86 met		Func- 30		_			_	_	_														_						peat subg	f _{MA} × 30							PH4							PHL1					_	
		Subgroup Syn			Tc = 25°C tion																											9 tw							4							á						
		Subg				2																										\	0						+							+						

See footnotes at end of table III.

TABLE III. Group A inspection for device type 04 - Continued.

		Chit		ns	=	-	=	-		-	=	=	=	-	=.	=		: -	-	=	=	=	-	-	=	=	=		-	-	-	=	=		=	=
		ø	Мах	0.6	8.0	11.0	=			13.0	=			0.6	8.0	7.0		: =	115			=	13.5	14.5	15.5	15.5	14.5	14.5	14.5	=	=	=	14.0	=	=	-
		Limits	Min	4.0	3.5	5.0	=	-	-	5.5	=		=	2.5	3.0	2.0		: =	9			=	5.0	2.0	0.9		=	=	5.5	=	=	=	4.5		=	=
		Measured terminal		CPU to TGU	CPU to TCU	PL to 00	PL to Q1	PL to Q2	PL to Q3	PL to Q0	PL to Q1	PL to Q2	PL to Q3	CPD to \overline{TCD}	CPD to TCD	Po to Qo	1 to Q1	2 to Q2	2000	P1 to Q1	P2 to Q2	3 to Q3	MR to Tau	MR to TOD	PL to TGU	to TOD	to TCU	to TOD	Po to TCU	P1 to TCU	P2 to TGU	P3 to TCU	Po to TGU	P1 to TCU	P2 to TGU	P3 to TCU
-	16	20 M	Vcc	5.0 V CPI	" CPI	I G.	I G.	I	<u>ا</u>	16	I G.		I	CPE	" CPE	п.	<u>.</u> .		_ a		<u>.</u>	<u>.</u>	" MR	" MR	PL	" P	Id	<u>.</u> 곱	- B	 P1	" P2	- B3	Po	" P1	" P2	- B3
-	5		N0	5.	0.0 V	2.7 V	0.0 V			0.0 V	_			_		Z			2	_					0.0 V			0.0 V	z				Z			
-				>		2.7	0.0																										_			
open).	4	18	MR	0.0 V	0.0 V					0.0 V	=		=		-		- !	: :	-	=		=		Z	0.0 V			۲ 0.0 ۷	=	=	-	=	=	=	=	-
8 V; or	13	17	<u>70</u>											TUO	OUT									TUO		TUO		OUT								
$ow \le 0$.	12	15	TOU	TUO	OUT																		OUT		TUO		TUO		TUO	=	=	=	=	=	=	=
2.0 V; I	-	14	Ы	77	=	≥	=	=		=	=	=	=	/2	/2	0.0 V		: =	=	=	=	=	77	/7	롣	=	=	=	0.0 V	=	=	=	=	=	=	=
≥ high ≥	10	13	P2			0.0 V	0.0 V	2.7 V	0.0 V	=	=			=				Z			Z							0.0 V			Z				Z	
may be	თ	12	Ь3			0.0 V	=	=	2.7 V	0.0 V	=		=	=	=			2	≧			Z						0.0 V				Z				Z
gnated	ω	10	GND	GND	=	=	=	=		=	=			=			- -		-	=		=		=		=	=	=	=	=	=	=	=		=	=
not desi	۲	6	603						OUT				OUT					Ē	5			OUT														
s (pins ı	9	8	075					OUT				OUT					į	100			OUT															
Terminal conditions (pins not designated may be high $\geq 2.0 \text{ V}$; low $\leq 0.8 \text{ V}$; or open)	c 2	7	CPU	Z	Z	0.0 V	=	=		=	=		=			0.0 V		: -	-	-	=	=		2.7 V	0.0 V		0.0 V	2.7 V	0.0 V	=	=	=	=		=	=
ninal co	4	2	CPD		2.7 V	0.0 V	=			=	=			Z	Z	0.0 V	- -	: =	-	=	=	=		0.0 V				0.0 V								
	ო		00			OUT				OUT						OUT			F	3																
-	7	ဇ	۵1				OUT				OUT						OUT			TUO																
	Ψ-	2	Ы			0.0 V		0.0 V		=			=		=		z	$\frac{1}{1}$	1	Z								0.0 V		Z				N.		
	Cases E, F		Ö.	146		148 0			151	152	153	154	155	156	157	158		60	10	163	64	65	99	167	168	169	170		172	173	174	175	176	177	178	179
			Tes			1	<u>_</u>	1	1	-	<u></u>	1	1	1.	-	1,	_	- -	-	<u> </u>	Ţ	-	1	1	_	1	1	1	_	_	_	_	_	1	_	_
	MIL-STD-	ool 883 method		3003	2 Fig. 4	-	-	-	-		-	-	-		-		_		-	=	=	=			=		=	-		=	=	-		-	-	-
		up Symbol		tрш2	°C tPHL2	PLH3				PHL3				PLH4	PHL4	PLH5			i	PHLS			РГН6	PHL6	PLH7	PLH8	PHL7	PHL8	ьпна ВПН3				PHL9			
		Subgroup		တ	$T_{\rm C}=25^{\circ}{\rm C}$	_																	_													

See footnotes at end of table III.

TABLE III. Group A inspection for device type 04 - Continued.

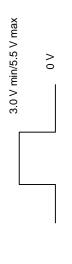
Terminal conditions (pins not designated may be high ≥ 2.0 V; low ≤ 0.8 V; or open).

		.=															
		Ü	ı	su	=	=	-	=	=	=	=	=	=		-		
		Limits	Max	14.5	=	=	=	14.0	=	=	=	14.5		=	-		
		ڎٙ	Min	5.5	=	=	=	4.5	=	=	=	2.0					
		Measured terminal		P0 to TCD	P1 to TCD	P2 to TCD	P3 to TCD	P0 to TCD	P1 to TCD	P2 to TCD	P3 to TCD	MR to Q0	MR to Q1	MR to Q2	MR to Q3		
	16	20	Vcc	2.0 V	=	=	=	=	=	=	=		-	=	=		
	15	19	PO	Z	0.0 V	=	=	Z	0.0 V			2.7 V	0.0 V		=		
	14	18	MR	0.0 V	=	=	=	=	=	=	=	Z	=		=		
5,	13	17	15 C	OUT	=	=	=	=	=	=	=						
	12	15	TOT														
5,	11	14	님	0.0 V	=	=	=	-	=	-	=	2/	=		=		
1	10	13	P2	0.0 V	0.0 V	<u>≥</u>	0.0 V	=	=	<u> </u>	0.0 V		=	2.7 V	0.0 V		
3	6	12	Р3	0.0 V	=	=	Z	0.0 V	=	=	Z	0.0 V			2.7 V		
grade	8	10	GND	GND	=	=	=	=	=	=	=	-	=		=		
200	7	6	0 3												OUT	n table I.	
2 2	9	8	07											OUT		limits fror	
	2	7	CPU	2.7 V	=	=	=	=	=	=	=	0.0 V	=	=	=	°C and use	= -55°C.
	4	2	CPD	0.0 V	=	=	=	=	=	=	=	=	=		=	$\Gamma_{\rm C} = +125^{\circ}$	except T _C
-	3	4	8									OUT				except ⁻	group 10,
	2	3	δ										OUT			subgroup !	as for sub
	٢	2	P1	0.0 V	Z	0.0 V			Z	0.0 V	=		2.7 V	0.0 V	0.0 V	ons as for	and limits.
	Cases E, F	Cases 2, X <u>1</u> /	Test no.	180	181	182	183	184	185	186	187	188	189	190	191	Same tests and terminal conditions as for subgroup 9, except T _C = +125°C and use limits from table	Same tests, terminal conditions and limits as for subgroup 10, except $T_{\rm C}$ = -55°C.
	MIL-STD-	883 method		3003	-	=	=	=	-	-	-					sts and tern	sts, termina
		Symbol		фргн10				PHL10				PHL11				Same te:	Same te
		Subgroup Symbol		6	$T_{\rm C} = 25^{\circ}{\rm C}$			I.				1				10	11
								+				+				•	

1/ For cases X and 2, pins not referenced are NC.

2/ Apply one pulse prior to measurement.

3.0 V min/5.5 V max



3/ For device type 02, Circuit A, the IL1 minimum and maximum test limits of measured terminal SR, shall be the same as those listed for the IL2 test, Circuit A, herein.

		Circuit	Circuit	Circuit	Circuit
Parameter	Device	Α	В	0	Q
IL1	IIV	25/-0.6	9:0-/80:-	25/-0.6	9'0-/0
11.2	01, 02	50/-1.2	06/-1.2	50/-1.2	9'0-/0
11.2	03, 04	75/-1.8	09/-1.8	50/-1.8	

 $\underline{4}$ For types 01 and 02, set outputs to 15th count (P0, P1, P2, P3 = 1), prior to measurement.

 $\underline{5}/$ H \geq 1.5 V, L \leq 1.5 V, A = 3.0 V minimum; B = 0.0 V or GND.

 $\underline{6}/$ Perform function sequence at V_{cc} = 4.5 V and repeat at V_{cc} = 5.5 V.

 $\overline{2}$ / The \mathfrak{f}_{MAX} minimum limit specified is the frequency of the input pulse. The output frequency shall be one-half of the input frequency.

 $\underline{8}$ For types 01 and 02, increment such that measurement of the specified output can occur on the next applied CP.

9/ f_{Max} shall be measured only under the conditions of initial qualification and after process or design changes which may affect this parameter. For all other conditions, f_{Max} shall be guaranteed, if not tested, to the limits specified in table III, herein.

5. PACKAGING

5.1 <u>Packaging requirements.</u> For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When actual packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activity within the Military Service or Defense Agency, or within the military service's system command. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

- 6.1 <u>Intended use.</u> Microcircuits conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.
 - 6.2 Acquisition requirements. Acquisition documents should specify the following:
 - a. Title, number, and date of the specification.
 - b. PIN and compliance identifier, if applicable (see 1.2).
 - c. Requirements for delivery of one copy of the conformance inspection data pertinent to the device inspection lot to be supplied with each shipment by the device manufacturer, if applicable.
 - d. Requirements for certificate of compliance, if applicable.
 - e. Requirements for notification of change of product or process to contracting activity in addition to notification to the qualifying activity, if applicable.
 - Requirements for failure analysis (including required test condition of method 5003 of MIL-STD-883), corrective action, and reporting of results, if applicable.
 - g. Requirements for product assurance options.
 - h. Requirements for special carriers, lead lengths, or lead forming, if applicable. These requirements should not affect the part number. Unless otherwise specified, these requirements will not apply to direct purchase by or direct shipment to the Government.
 - i. Requirements for "JAN" marking.
 - j. Packaging requirements (see 5.1).
- 6.3 <u>Superseding information</u>. The requirements of MIL-M-38510 have been superseded to take advantage of the available Qualified Manufacturer Listing (QML) system provided by MIL-PRF-38535. Previous references to MIL-M-38510 in this document have been replaced by appropriate references to MIL-PRF-38535. All technical requirements now consist of this specification and MIL-PRF-38535. The MIL-M-38510 specification sheet number and PIN have been retained to avoid adversely impacting existing government logistics systems and contractor's parts lists.
- 6.4 <u>Qualification</u>. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List QML-38535 whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or purchase orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from DSCC-VQ, 3990 E. Broad Street, Columbus, Ohio 43123-1199.

6.5 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331, and as follows:

GND	Ground zero voltage potential
V _{IN}	Voltage level at an input terminal
I _{IN}	Current flowing into an input terminal

- 6.6 <u>Logistic support.</u> Lead materials and finishes (see 3.4) are interchangeable. Unless otherwise specified, microcircuits acquired for Government logistic support will be acquired to device class B (see 1.2.2), lead material and finish A (see 3.4). Longer length leads and lead forming should not affect the part number.
- 6.7 <u>Substitutability.</u> The cross-reference information below is presented for the convenience of users. Microcircuits covered by this specification will functionally replace the listed generic-industry type. Generic-industry microcircuit types may not have equivalent operational performance characteristics across military temperature ranges or reliability factors equivalent to MIL-M-35810 device types and may have slight physical variations in relation to case size. The presence of this information should not be deemed as permitting substitution of generic-industry types for MIL-M-38510 types or as a waiver of any of the provisions of MIL-PRF-38535.

Military device	Generic-industry						
type	type						
01	54F161A						
02	54F163A						
03	54F191						
04	54F193						

6.8 <u>Manufacturers' designation.</u> Manufacturers' circuits which form a part of this specification are designated with an "X" as shown in table IV herein.

TABLE IV. Manufacturers' designations.

Device	A	В	С	D
type	National Semiconductor	Motorola Inc.		Texas
			Čorp.	Instruments
01	X		X	X
02	X		Х	X
03	X			
04	X			

6.9 <u>Changes from previous issue.</u> Marginal notations are not used in this revision to identify changes with respect to the previous issue due to the extensiveness of the changes.

Preparing activity: DLA - CC Custodians: Army - CR Navy - EC Air Force - 11

(Project 5962-2026) DLA - CC

Review activities: Army - MI, SM Navy - AS, CG, MC, SH, TD Air Force - 03, 19, 99

NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at www.dodssp.daps.mil.